

First Tests of Radiation Hardness & Serial Test Setup

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Irradiation Protocol - ^{60}Co source



FACHBEREICH 07
Mathematik
und Informatik,
Physik, Geographie

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25.02.2014

Rücksendung der bestrahlten Elektronik

Hallo Werner,

wie gefordert haben wir die Elektronik im Strahlencentrum mit Cobalt Quellen bestrahlt.

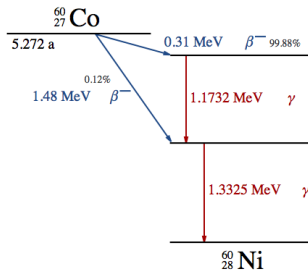
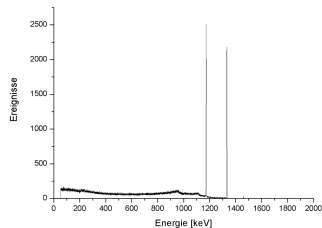
Das aktive Bauteil hat eine Strahlungsdosis äquivalent zu 30kGy abbekommen (verglichen mit unserer Bestrahlung von PWO-II) und lief die ganze Zeit ohne Anstieg des Stroms oder der Temperatur.

Die nicht aktive Elektronik hat eine Gesamtdosis von 8kGy abbekommen (verglichen mit unserer Bestrahlung von PWO-II).

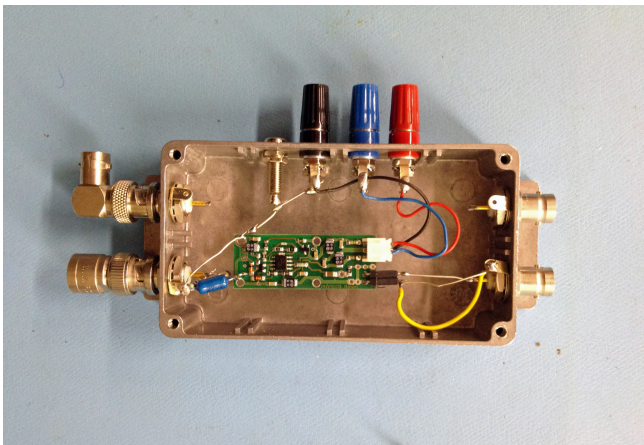
Die Dosisaangaben beziehen sich immer auf das, was PWO absorbiert hätte. Die Elektronik absorbiert natürlich deutlich weniger und so ist die Dosisaangabe immer auf die Umgebung zu beziehen.

Mit freundlichen Grüßen,

Till Kuske

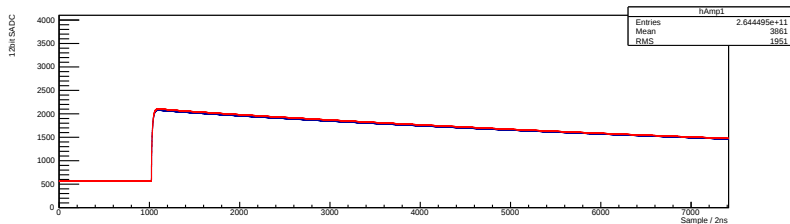
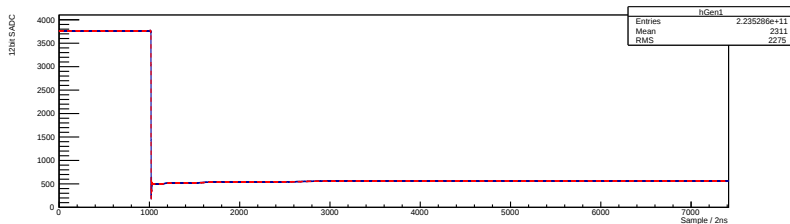


Basel LNP PreAmp inside the Testbox



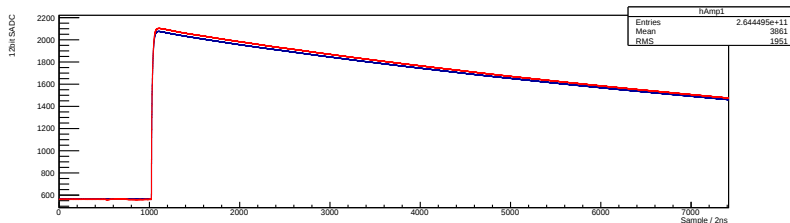
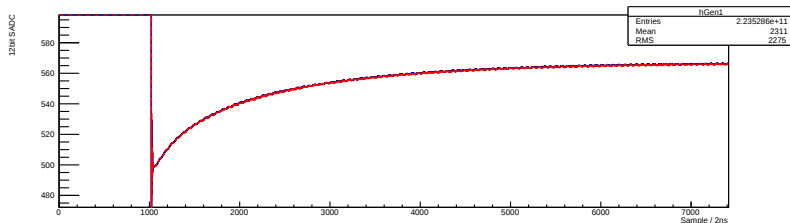
Before and after irradiation of LNP, SN 284

Irradiation of "7 kGy"; -before -after

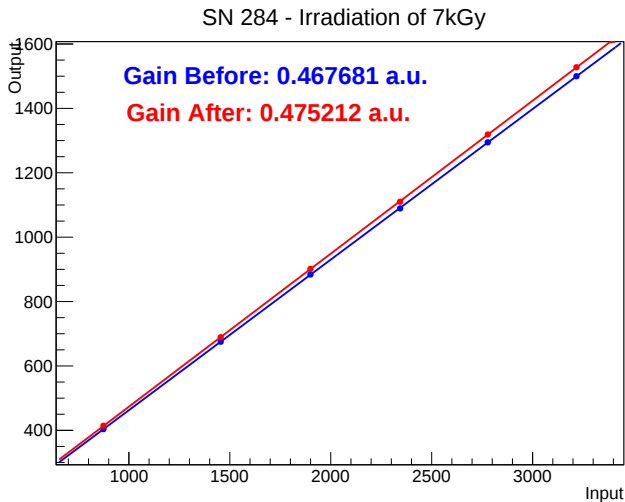


Zoom - Before and after irradiation of LNP, SN 284

Irradiation of "7 kGy"; -before -after

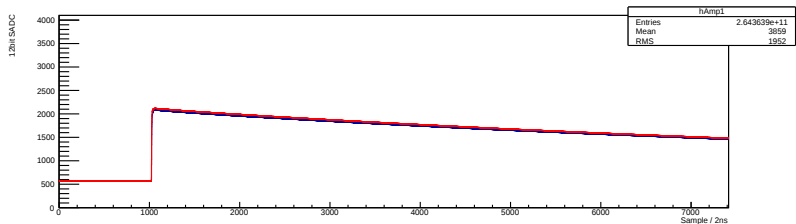
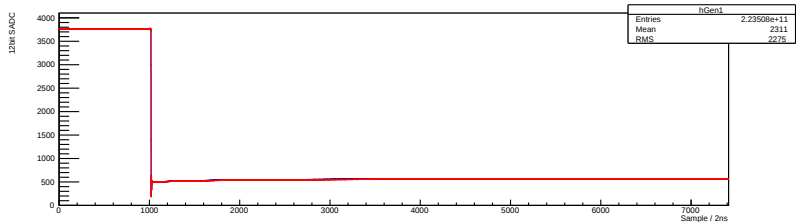


Gain Change: 1.6%, SN 284

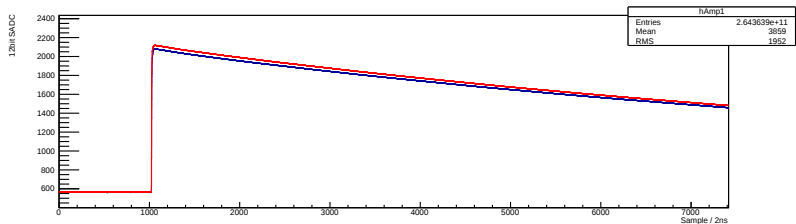
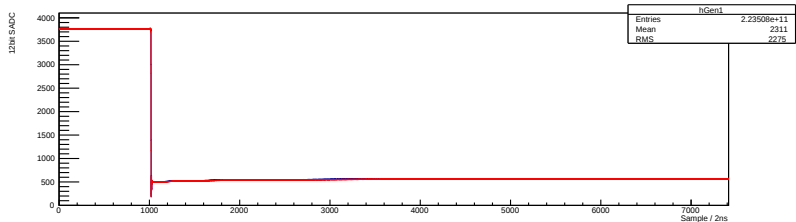


Before and after irradiation of LNP, SN 283

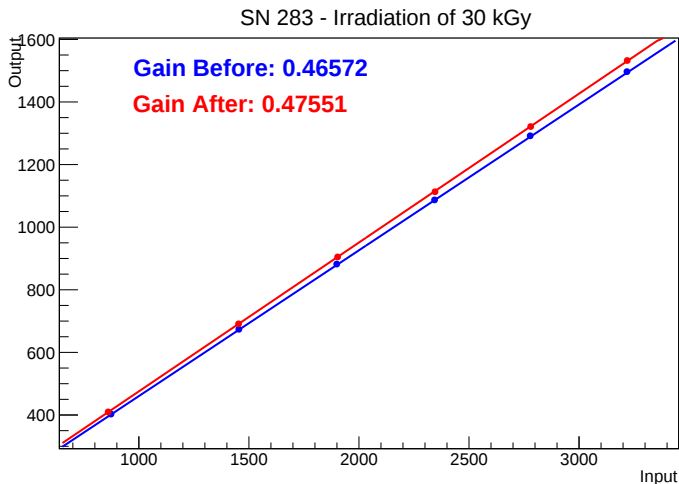
Irradiation of "30 kGy" and Power ON ($\pm 6V$); **–before** **–after**



Zoom - Before and after irradiation of LNP, SN 283

Irradiation of "30 kGy" and Power ON ($\pm 6V$); **—before** **—after**

Gain Change: 2.1%, SN 283



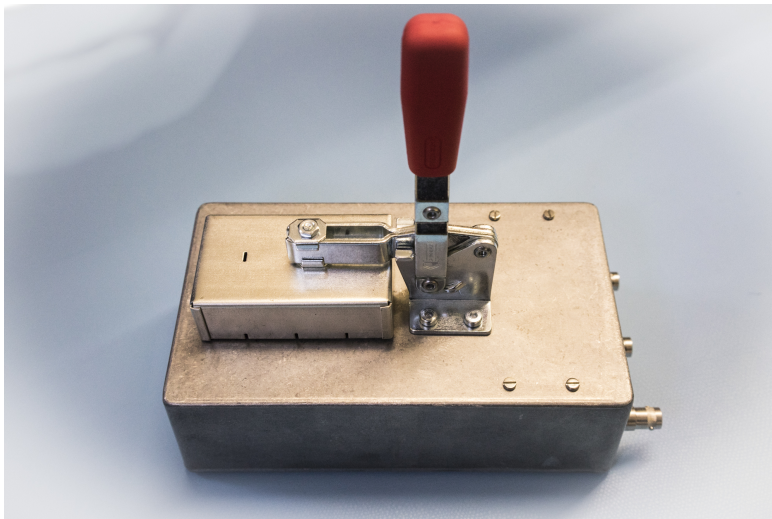
Power Consumption

After irradiation current is decreased for both PreAmps

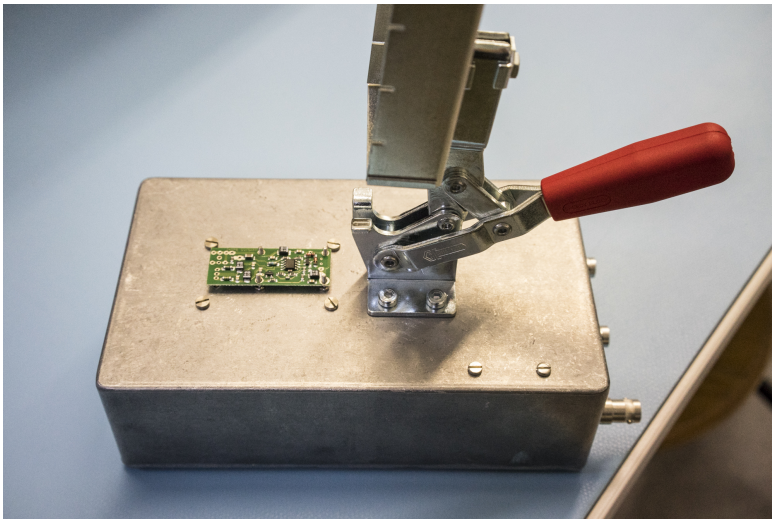
		SN 283		SN 284	
		no pulser	pulser	no pulser	pulser
+6 V	before	635 uA	648 uA	630 uA	657 uA
	after	600 uA	609 uA	587 uA	596 uA
-6 V	before	126 uA	155 uA	119 uA	146 uA
	after	115 uA	134 uA	110 uA	120 uA

Test Setup

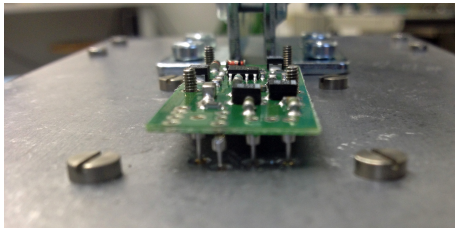
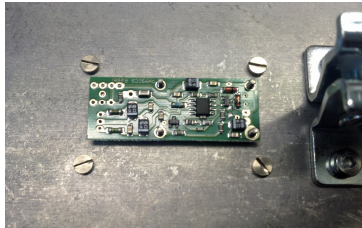
Test Box for APD PreAmp's



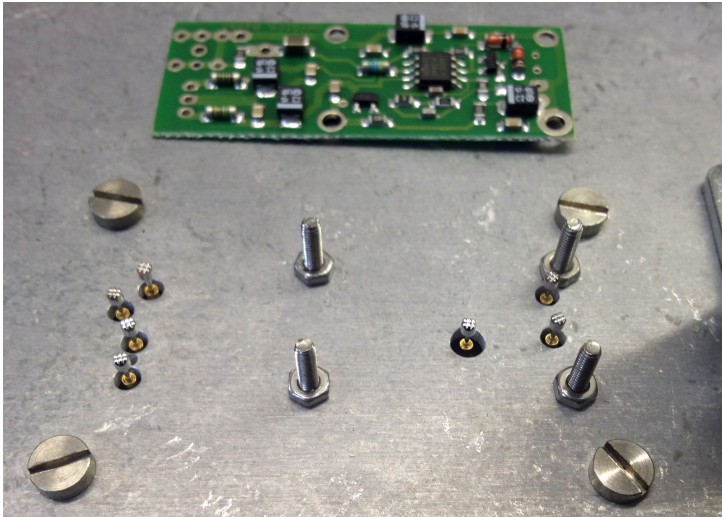
Open Test Box for APD PreAmp's



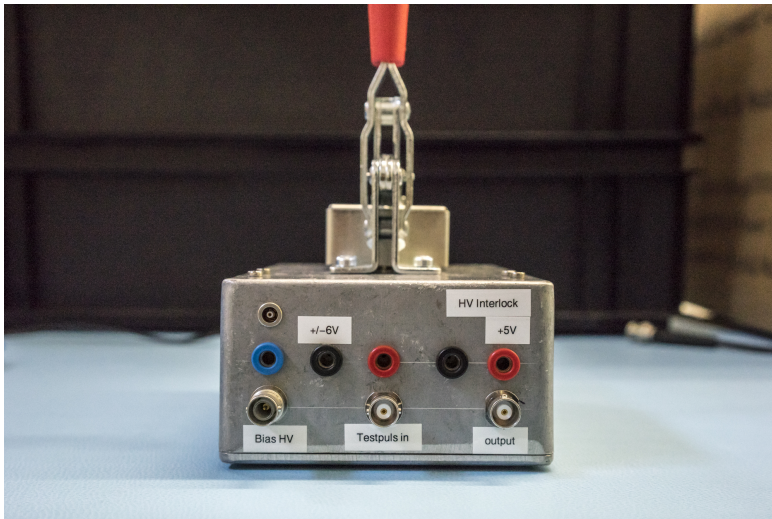
Preamplifier Fixation



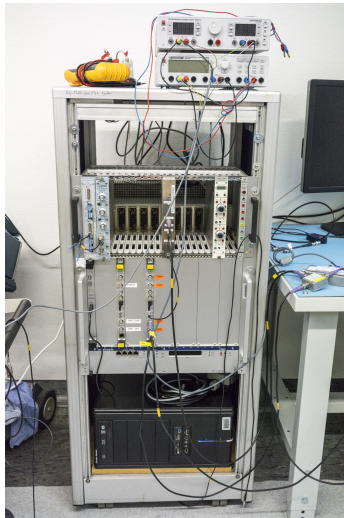
Needle Bed



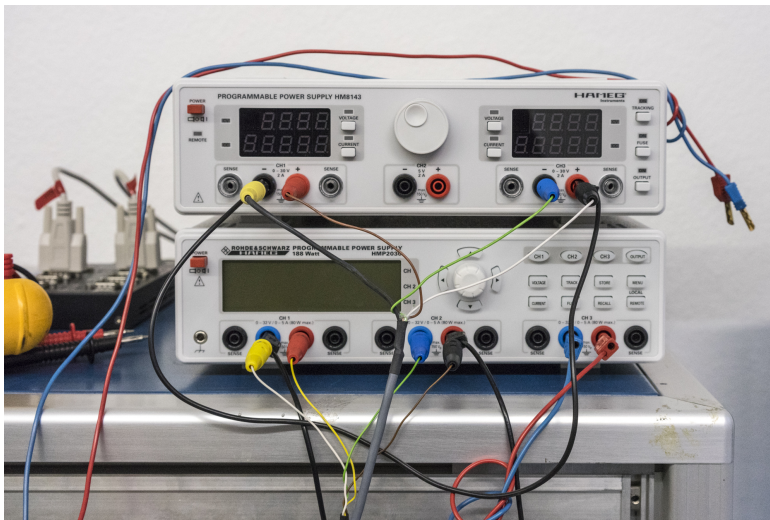
Connections Test Box for APD PreAmp's



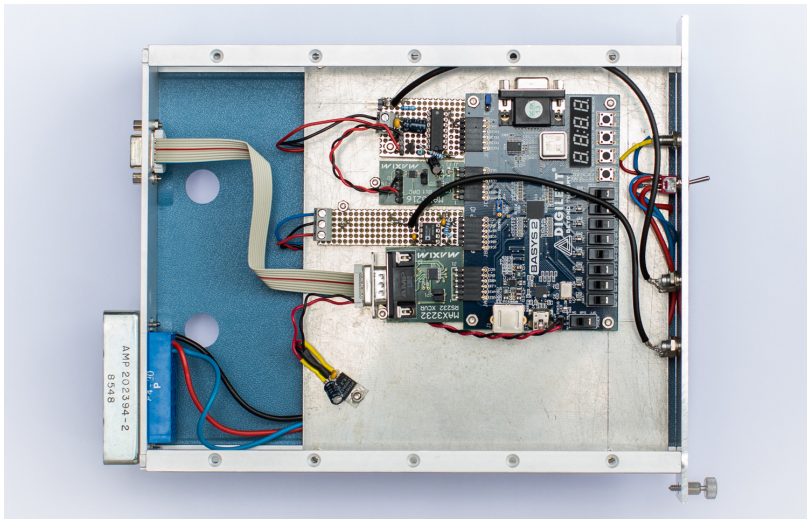
Test Rack



Power Supplies



NIM FPGA Pulser Module



Summary

- First Test of Radiation Hardness
- Irradiation of 7 kGy - 1.6% gain change
- Irradiation of 30 kGy - 2.1% gain change

Summary

- First Test of Radiation Hardness
- Irradiation of 7 kGy - 1.6% gain change
- Irradiation of 30 kGy - 2.1% gain change
- Test Box for APD PreAmp's is ready